

Jamie D Phillips

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

157
papers

3,926
citations

33
h-index

57
g-index

180
ext. papers

4,446
ext. citations

3
avg, IF

5.41
L-index

#	Paper	IF	Citations
157	A Light-Tolerant Wireless Neural Recording IC for Motor Prediction With Near-Infrared-Based Power and Data Telemetry. <i>IEEE Journal of Solid-State Circuits</i> , 2022 , 1-1	5.5	2
156	Effects of high temperature annealing on the atomic layer deposited HfO ₂ /EGa ₂ O ₃ (010) interface. <i>Journal of Applied Physics</i> , 2022 , 131, 035106	2.5	2
155	Tracking the Migration of the Monarch Butterflies with the World's Smallest Computer. <i>GetMobile (New York, N Y)</i> , 2022 , 26, 25-29	0.8	
154	Bridging the "Last Millimeter" Gap of Brain-Machine Interfaces via Near-Infrared Wireless Power Transfer and Data Communications. <i>ACS Photonics</i> , 2021 , 8, 1430-1438	6.3	6
153	Memristors Based on (Zr, Hf, Nb, Ta, Mo, W) High-Entropy Oxides. <i>Advanced Electronic Materials</i> , 2021 , 7, 2001258	6.4	9
152	A Light Tolerant Neural Recording IC for Near-Infrared-Powered Free Floating Motes. 2021 , 2021,		3
151	Mid-wave infrared transmittance filters in suspended GaAs subwavelength gratings. <i>Applied Physics Letters</i> , 2021 , 119, 031103	3.4	2
150	Thermoradiative Cell Equivalent Circuit Model. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 928-930	2.9	0
149	Charge trapping and recovery in ALD HfO ₂ /EGa ₂ O ₃ (010) MOS capacitors. <i>Semiconductor Science and Technology</i> , 2021 , 36, 04LT01	1.8	4
148	Highly selective GaAs/AlGaAs dry etching using HBr/SF ₆ /He. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021 , 39, 052202	1.3	
147	Demonstration of a GaSb/GaAs Quantum Dot Intermediate Band Solar Cell Operating at Maximum Power Point. <i>Physical Review Letters</i> , 2020 , 125, 247703	7.4	2
146	A 0.190.17mm Wireless Neural Recording IC for Motor Prediction with Near-Infrared-Based Power and Data Telemetry.. <i>Digest of Technical Papers - IEEE International Solid-State Circuits Conference</i> , 2020 , 2020, 416-418	4	9
145	Mid-wave infrared filtering in silicon subwavelength zero-contrast gratings 2020 ,		2
144	Polarization-independent narrowband transmittance filters via symmetry-protected modes in high contrast gratings. <i>Optics Letters</i> , 2020 , 45, 4348-4351	3	8
143	Dual-Junction GaAs Photovoltaics for Low Irradiance Wireless Power Transfer in Submillimeter-Scale Sensor Nodes. <i>IEEE Journal of Photovoltaics</i> , 2020 , 10, 1721-1726	3.7	3
142	Indoor Photovoltaics Based on AlGaAs 2020 , 241-271		1
141	Surface morphology and straight crack generation of ultrafast laser irradiated EGa ₂ O ₃ . <i>Journal of Applied Physics</i> , 2019 , 125, 223104	2.5	6

140	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 2489-2495	2.9	15
139	High-Efficiency Photovoltaic Modules on a Chip for Millimeter-Scale Energy Harvesting. <i>Progress in Photovoltaics: Research and Applications</i> , 2019 , 27, 540-546	6.8	10
138	InGaAs/GaAsSb Type-II Superlattices for Short-Wavelength Infrared Detection. <i>Journal of Electronic Materials</i> , 2019 , 48, 6025-6029	1.9	4
137	Carrier dynamics of intermediate sub-bandgap transitions in ZnTeO. <i>Journal of Applied Physics</i> , 2019 , 126, 135701	2.5	0
136	Low damage electrical modification of 4H-SiC via ultrafast laser irradiation. <i>Journal of Applied Physics</i> , 2018 , 123, 145106	2.5	4
135	Analysis of Carrier Transport in n-Type Hg _{1-x} Cd _x Te with Ultra-Low Doping Concentration. <i>Journal of Electronic Materials</i> , 2018 , 47, 5699-5704	1.9	1
134	A 179-Lux Energy-Autonomous Fully-Encapsulated 17-mm ³ Sensor Node with Initial Charge Delay Circuit for Battery Protection 2018 ,		7
133	Influence of Subwavelength Grating Asymmetry on Long-Wavelength Infrared Transmittance Filters. <i>IEEE Photonics Journal</i> , 2018 , 10, 1-8	1.8	2
132	Subcutaneous Photovoltaic Infrared Energy Harvesting for Bio-Implantable Devices. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2432-2437	2.9	46
131	. <i>IEEE Journal of Photovoltaics</i> , 2017 , 7, 508-512	3.7	16
130	Long-wavelength infrared transmission filters via two-step subwavelength dielectric gratings. <i>Optics Letters</i> , 2017 , 42, 518-521	3	8
129	Analysis of the intermediate-band absorption properties of type-II GaSb/GaAs quantum-dot photovoltaics. <i>Physical Review B</i> , 2017 , 96,	3.3	22
128	Infrared Energy Harvesting in Millimeter-Scale GaAs Photovoltaics. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4554-4560	2.9	5
127	Variable-Field Hall Effect Analysis of HgCdTe Epilayers with Very Low Doping Density. <i>Journal of Electronic Materials</i> , 2017 , 46, 5479-5483	1.9	1
126	Small-area Si Photovoltaics for Low-Flux Infrared Energy Harvesting. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 15-20	2.9	14
125	Energy Harvesting for GaAs Photovoltaics Under Low-Flux Indoor Lighting Conditions. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2820-2825	2.9	39
124	Investigating Student Motivation and Performance in Electrical Engineering and Its Subdisciplines. <i>IEEE Transactions on Education</i> , 2016 , 59, 241-247	2.1	3
123	Chemical epitaxy and interfacial reactivity in solution deposited PbS on ZnTe. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 1996-2002	7.1	6

122	The effect of doping on low temperature growth of high quality GaAs nanowires on polycrystalline films. <i>Nanotechnology</i> , 2016 , 27, 495605	3.4	3
121	A >78%-Efficient Light Harvester over 100-to-100klux with Reconfigurable PV-Cell Network and MPPT Circuit. <i>Digest of Technical Papers - IEEE International Solid-State Circuits Conference</i> , 2016 , 2016, 370-371	4	25
120	AlGaAs Photovoltaics for Indoor Energy Harvesting in mm-Scale Wireless Sensor Nodes. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2170-2175	2.9	56
119	Heterojunction Band Offset Limitations on Open-Circuit Voltage in p-ZnTe/n-ZnSe Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2015 , 5, 874-877	3.7	4
118	Normal incidence narrowband transmission filtering capabilities using symmetry-protected modes of a subwavelength, dielectric grating. <i>Optics Letters</i> , 2015 , 40, 2637-40	3	22
117	Dual color longwave InAs/GaSb type-II strained layer superlattice detectors. <i>Infrared Physics and Technology</i> , 2015 , 70, 93-98	2.7	5
116	Intrinsically switchable, high-Q ferroelectric-con-silicon composite film bulk acoustic resonators. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2014 , 61, 231-8	3.2	22
115	Multiphoton Sub-Band-Gap Photoconductivity and Critical Transition Temperature in Type-II GaSb Quantum-Dot Intermediate-Band Solar Cells. <i>Physical Review Applied</i> , 2014 , 1,	4.3	25
114	Resolving spectral overlap issue of intermediate band solar cells using non-uniform sub-bandgap state filling. <i>Progress in Photovoltaics: Research and Applications</i> , 2014 , 22, 1062-1069	6.8	4
113	Nanodot formation induced by femtosecond laser irradiation. <i>Applied Physics Letters</i> , 2014 , 105, 163103	3.4	10
112	Intermediate Band to Conduction Band Optical Absorption in ZnTeO. <i>IEEE Journal of Photovoltaics</i> , 2014 , 4, 1091-1094	3.7	8
111	Passivation of long-wave infrared InAs/GaSb superlattice detectors with epitaxially grown ZnTe 2014 ,		3
110	Distinguishing Optical Behavior of Oxygen States and Native Deep Level Emission in ZnTe. <i>Journal of Electronic Materials</i> , 2014 , 43, 879-883	1.9	5
109	Oxygen Incorporation in ZnTeO Alloys via Molecular Beam Epitaxy. <i>Journal of Electronic Materials</i> , 2014 , 43, 889-893	1.9	4
108	Transport properties of ZnTe:N thin films. <i>Applied Physics Letters</i> , 2013 , 103, 042108	3.4	7
107	Intrinsically Switchable Ferroelectric Contour Mode Resonators. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2013 , 61, 2806-2813	4.1	5
106	A new class of room-temperature multiferroic thin films with bismuth-based supercell structure. <i>Advanced Materials</i> , 2013 , 25, 1028-32	24	66
105	Intermediate band solar energy conversion in ZnTeO 2013 ,		2

104	Epitaxial growth of ZnTe on GaSb(100) using in situ ZnCl ₂ surface clean. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C118	1.3	
103	Preserving voltage and long wavelength photoresponse in GaSb/GaAs quantum dot solar cells 2013 ,		4
102	The disintegration of GaSb/GaAs nanostructures upon capping. <i>Applied Physics Letters</i> , 2013 , 102, 113103	3.4	26
101	. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1488-1493	2.9	12
100	Mid-wave infrared HgCdTe nBn photodetector. <i>Applied Physics Letters</i> , 2012 , 100, 161102	3.4	86
99	Design of an Auger-Suppressed Unipolar HgCdTe NBN Photodetector. <i>Journal of Electronic Materials</i> , 2012 , 41, 2886-2892	1.9	35
98	Thermal emission in type-II GaSb/GaAs quantum dots and prospects for intermediate band solar energy conversion. <i>Journal of Applied Physics</i> , 2012 , 111, 074514	2.5	33
97	Broadband long-wavelength infrared Si/SiO ₂ subwavelength grating reflector. <i>Optics Letters</i> , 2012 , 37, 1523-5	3	18
96	Room temperature strong coupling effects from single ZnO nanowire microcavity. <i>Optics Express</i> , 2012 , 20, 11830-7	3.3	21
95	Intrinsically switchable thin film ferroelectric resonators 2012 ,		7
94	A DC voltage dependent switchable acoustically coupled BAW filter based on BST-on-silicon composite structure 2012 ,		5
93	Decoupling spectral overlap of intermediate band solar cells using low-high state filling 2012 ,		1
92	Illumination instabilities in ZnO/HfO ₂ thin-film transistors and influence of grain boundary charge. <i>Journal of Materials Research</i> , 2012 , 27, 2199-2204	2.5	5
91	Atomic Resolution TEM Study on Quantum Dots in ZnSe/ZnTe Heterostructure. <i>Microscopy and Microanalysis</i> , 2011 , 17, 1646-1647	0.5	
90	ZnO nanorods for simultaneous light trapping and transparent electrode application in solar cells 2011 ,		1
89	Predicted Performance Improvement of Auger-Suppressed HgCdTe Photodiodes and nBn Heterojunction Detectors. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 501-507	2.9	34
88	Intermediate-band solar cells based on dilute alloys and quantum dots. <i>Frontiers of Optoelectronics in China</i> , 2011 , 4, 2-11		5
87	Design and Modeling of HgCdTe nBn Detectors. <i>Journal of Electronic Materials</i> , 2011 , 40, 1624-1629	1.9	47

86	ZnO/ZnSe/ZnTe Heterojunctions for ZnTe-Based Solar Cells. <i>Journal of Electronic Materials</i> , 2011 , 40, 1674-1678	1.9	22
85	Admittance Spectroscopy of Interface States in ZnO/HfO_2 Thin-Film Electronics. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1713-1715	4.4	7
84	Arsenic Diffusion Study in HgCdTe for Low p-Type Doping in Auger-Suppressed Photodiodes. <i>Journal of Electronic Materials</i> , 2010 , 39, 945-950	1.9	8
83	MWIR and LWIR HgCdTe Infrared Detectors Operated with Reduced Cooling Requirements. <i>Journal of Electronic Materials</i> , 2010 , 39, 873-881	1.9	24
82	An Intrinsically Switchable FBAR Filter Based on Barium Titanate Thin Films. <i>IEEE Microwave and Wireless Components Letters</i> , 2009 , 19, 359-361	2.6	28
81	Parameter extraction of HgCdTe infrared photodiodes exhibiting Auger suppression. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 234003	3	12
80	Drift-Diffusion Modeling for Impurity Photovoltaic Devices. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 3168-3174	2.9	62
79	Optical Characteristics of ZnTeO Thin Films Synthesized by Pulsed Laser Deposition and Molecular Beam Epitaxy. <i>Journal of Electronic Materials</i> , 2009 , 38, 119-125	1.9	34
78	Intermediate-band photovoltaic solar cell based on ZnTe:O. <i>Applied Physics Letters</i> , 2009 , 95, 011103	3.4	168
77	Model for intermediate band solar cells incorporating carrier transport and recombination. <i>Journal of Applied Physics</i> , 2009 , 105, 064512	2.5	54
76	Generation and recombination rates at ZnTe:O intermediate band states. <i>Applied Physics Letters</i> , 2009 , 95, 261107	3.4	47
75	Intrinsically switchable contour mode acoustic wave resonators based on barium titanate thin films 2009 ,		5
74	Complementary Thin-Film Electronics Based on n-Channel ZnO and p-Channel ZnTe. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1314-1316	4.4	20
73	Growth and structural properties of m-plane ZnO on MgO (001) by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2008 , 92, 233505	3.4	50
72	Optimization of random diffraction gratings in thin-film solar cells using genetic algorithms. <i>Solar Energy Materials and Solar Cells</i> , 2008 , 92, 1689-1696	6.4	81
71	Quantum Confinement and Carrier Localization Effects in ZnO/Mg _x Zn _{1-x} O Wells Synthesized by Pulsed Laser Deposition. <i>Journal of Electronic Materials</i> , 2008 , 37, 749-754	1.9	9
70	Modeling of LWIR HgCdTe Auger-Suppressed Infrared Photodiodes under Nonequilibrium Operation. <i>Journal of Electronic Materials</i> , 2008 , 37, 1362-1368	1.9	25
69	Electrical Characteristics and Photoresponse of ZnO/ZnTe Heterojunction Diodes. <i>Journal of Electronic Materials</i> , 2008 , 37, 1044-1048	1.9	19

68	Improving Linearity of Ferroelectric-Based Microwave Tunable Circuits. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2007 , 55, 354-360	4.1	24
67	Electrical Characteristics of PEDOT:PSS Organic Contacts to HgCdTe. <i>Journal of Electronic Materials</i> , 2007 , 36, 841-845	1.9	7
66	Modeling and Design Considerations of HgCdTe Infrared Photodiodes under Nonequilibrium Operation. <i>Journal of Electronic Materials</i> , 2007 , 36, 846-851	1.9	21
65	Hysteretic metal/ferroelectric/semiconductor capacitors based on PZT/ZnO heterostructures. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 2430-2434	3	43
64	A DC Voltage Dependant Switchable Thin Film Bulk Wave Acoustic Resonator Using Ferroelectric Thin Film. <i>IEEE MTT-S International Microwave Symposium Digest IEEE MTT-S International Microwave Symposium</i> , 2007 ,		34
63	Free carrier absorption and lattice vibrational modes in bulk ZnO. <i>Journal of Electronic Materials</i> , 2006 , 35, 525-529	1.9	21
62	Trap-related photoconductivity in ZnO epilayers. <i>Journal of Electronic Materials</i> , 2006 , 35, 543-549	1.9	66
61	ZnO thin-film transistors with polycrystalline (Ba,Sr)TiO ₃ gate insulators. <i>Applied Physics Letters</i> , 2006 , 88, 212903	3.4	91
60	Sub-bandgap photoconductivity in ZnO epilayers and extraction of trap density spectra. <i>Semiconductor Science and Technology</i> , 2006 , 21, 717-723	1.8	124
59	A Linearity Improvement Technique for Thin-film Barium Strontium Titanate Capacitors 2006 ,		16
58	Analysis and design optimization of electrooptic interferometric modulators for microphotronics applications. <i>Journal of Lightwave Technology</i> , 2006 , 24, 2340-2346	4	9
57	Electric field dependence of piezoelectric coefficient in ferroelectric thin films. <i>Journal of Electroceramics</i> , 2006 , 17, 613-617	1.5	12
56	Properties of ferroelectric Pb(Zr,Ti)O ₃ thin films on ZnO/Al ₂ O ₃ (0001) epilayers. <i>Thin Solid Films</i> , 2005 , 491, 301-304	2.2	12
55	Growth and electronic properties of ZnO epilayers by plasma-assisted molecular beam epitaxy. <i>Journal of Electronic Materials</i> , 2005 , 34, 699-703	1.9	13
54	Detailed study of above bandgap optical absorption in HgCdTe. <i>Journal of Electronic Materials</i> , 2005 , 34, 773-778	1.9	34
53	Properties of electrical contacts on bulk and epitaxial n-type ZnO. <i>Journal of Electronic Materials</i> , 2005 , 34, 389-394	1.9	20
52	Optical waveguiding in BaTiO ₃ /MgO/Al _x O _y /GaAs heterostructures. <i>Applied Physics Letters</i> , 2004 , 85, 5206-5208	3.4	10
51	Epitaxial growth and surface modeling of ZnO on c-plane Al ₂ O ₃ . <i>Applied Physics Letters</i> , 2004 , 85, 6338-6340	3.4	8

50	Electronic properties of ferroelectric BaTiO ₃ /MgO capacitors on GaAs. <i>Applied Physics Letters</i> , 2004 , 85, 3208-3210	3.4	23
49	Optical-absorption model for molecular-beam epitaxy HgCdTe and application to infrared detector photoresponse. <i>Journal of Electronic Materials</i> , 2004 , 33, 701-708	1.9	17
48	Pulsed laser annealing of self-organized InAs/GaAs quantum dots. <i>Journal of Electronic Materials</i> , 2004 , 33, L5-L8	1.9	12
47	Optical absorption studies of HgCdTe epitaxial layers for improved infrared detector modeling. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 662-665		
46	Far infrared modulated photoluminescence in InSb quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 22, 598-602	3	1
45	Optical absorption properties of HgCdTe epilayers with uniform composition. <i>Journal of Electronic Materials</i> , 2003 , 32, 646-650	1.9	15
44	Threading and misfit-dislocation motion in molecular-beam epitaxy-grown HgCdTe epilayers. <i>Journal of Electronic Materials</i> , 2003 , 32, 710-716	1.9	24
43	Absorption, carrier lifetime, and gain in InAs-GaAs quantum-dot infrared photodetectors. <i>IEEE Journal of Quantum Electronics</i> , 2003 , 39, 459-467	2	118
42	Deposition Of BaTiO ₃ Thin Films And MgO Buffer Layers On Patterned GaAs Substrates For Integrated Optics Applications. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 784, 11231		
41	Uniformity of optical absorption in HgCdTe epilayer measured by infrared spectromicroscopy. <i>Applied Physics Letters</i> , 2003 , 83, 3701-3703	3.4	12
40	Far-infrared modulated photoluminescence spectroscopy of InSb/GaSb quantum dot structures. <i>Physical Review B</i> , 2003 , 68,	3.3	13
39	Control of very-long-wavelength infrared HgCdTe detector-cutoff wavelength. <i>Journal of Electronic Materials</i> , 2002 , 31, 664-668	1.9	16
38	Advances in large-area Hg _{1-x} CdxTe photovoltaic detectors for remote-sensing applications. <i>Journal of Electronic Materials</i> , 2002 , 31, 726-731	1.9	10
37	Gain dynamics and ultrafast spectral hole burning in In(Ga)As self-organized quantum dots. <i>Applied Physics Letters</i> , 2002 , 81, 670-672	3.4	38
36	Lateral indium-indium pair correlations within the wetting layers of buried InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 2002 , 81, 1423-1425	3.4	11
35	Evaluation of the fundamental properties of quantum dot infrared detectors. <i>Journal of Applied Physics</i> , 2002 , 91, 4590-4594	2.5	214
34	Composition control of long wavelength MBE HgCdTe using In-situ spectroscopic ellipsometry. <i>Journal of Electronic Materials</i> , 2001 , 30, 643-646	1.9	17
33	Carrier dynamics in self-organized quantum dots and their application to long-wavelength sources and detectors. <i>Journal of Crystal Growth</i> , 2001 , 227-228, 27-35	1.6	20

32	Growth of HgCdTe for long-wavelength infrared detectors using automated control from spectroscopic ellipsometry measurements. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 1580		16
31	Optoelectronic Device Applications of Self-Organized In(Ga,Al)As/Ga(Al)As Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 618, 195		
30	Growth of InSb on GaAs using InAlSb buffer layers. <i>Journal of Crystal Growth</i> , 2000 , 209, 567-571	1.6	15
29	InAsSb/InPSb strained-layer superlattice growth using metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2000 , 211, 400-404	1.6	4
28	Exploring new active regions for type I InAsSb strained-layer lasers. <i>Journal of Electronic Materials</i> , 2000 , 29, 91-93	1.9	2
27	Quantum dot carrier dynamics and far-infrared devices 2000 , 4078, 84		2
26	Growth and electroluminescent properties of self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dots grown on silicon. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1116		3
25	Electron intersubband energy level spacing in self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dot lasers from temperature-dependent modulation measurements. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1276		2
24	Bistability and self-pulsation in quantum-dot lasers with intracavity quantum-dot saturable absorbers. <i>Applied Physics Letters</i> , 1999 , 74, 1654-1656	3.4	3 ¹
23	Pressure-induced energy level crossings and narrowing of photoluminescence linewidth in self-assembled InAlAs/AlGaAs quantum dots. <i>Applied Physics Letters</i> , 1999 , 74, 1549-1551	3.4	2 ⁰
22	Nanometer-scale studies of vertical organization and evolution of stacked self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 1999 , 74, 2824-2826	3.4	7 ¹
21	Self-organized In _{0.4} Ga _{0.6} As quantum-dot lasers grown on Si substrates. <i>Applied Physics Letters</i> , 1999 , 74, 1355-1357	3.4	7 ⁰
20	Interdiffusion and surface segregation in stacked self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 1999 , 75, 2797-2799	3.4	5 ⁶
19	Bias-controlled wavelength switching in coupled-cavity In _{0.4} Ga _{0.6} As/GaAs self-organized quantum dot lasers. <i>Applied Physics Letters</i> , 1999 , 74, 783-785	3.4	3 ¹
18	In(Ga)As/GaAs self-organized quantum dot light emitters grown on silicon substrates. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 1186-1189	1.6	1
17	Self-organized growth of In(Ga)As/GaAs quantum dots and their opto-electronic device applications. <i>Bulletin of Materials Science</i> , 1999 , 22, 519-529	1.7	3
16	In(Ga)As/GaAs self-organized quantum dot lasers: DC and small-signal modulation properties. <i>IEEE Transactions on Electron Devices</i> , 1999 , 46, 871-883	2.9	8 ¹
15	High-speed modulation of quantum-dot lasers 1999 ,		1

14	Self-assembled InAs-GaAs quantum-dot intersubband detectors. <i>IEEE Journal of Quantum Electronics</i> , 1999 , 35, 936-943	2	182
13	Temperature-dependent photoluminescence of In _{0.5} Al _{0.5} As/Al _{0.25} Ga _{0.75} As self-organized quantum dots. <i>Journal of Applied Physics</i> , 1999 , 85, 2997-2999	2.5	5
12	Characteristics of InAs/AlGaAs self-organized quantum dot modulation doped field effect transistors. <i>Applied Physics Letters</i> , 1998 , 72, 3509-3511	3.4	32
11	Far-infrared photoconductivity in self-organized InAs quantum dots. <i>Applied Physics Letters</i> , 1998 , 72, 2020-2022	3.4	209
10	Linear and quadratic electro-optic coefficients of self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dots. <i>Applied Physics Letters</i> , 1998 , 72, 1275-1277	3.4	31
9	Intersubband absorption and photoluminescence in Si-doped self-organized InAs/Ga(Al)As quantum dots. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 1343		11
8	Small-signal modulation and differential gain of single-mode self-organized In _{0.4} Ga _{0.6} As/GaAs quantum dot lasers. <i>Applied Physics Letters</i> , 1997 , 70, 2952-2953	3.4	75
7	Photoluminescence and far-infrared absorption in Si-doped self-organized InAs quantum dots. <i>Applied Physics Letters</i> , 1997 , 71, 2079-2081	3.4	70
6	Room temperature luminescence from self-organized quantum dots with high size uniformity. <i>Journal of Crystal Growth</i> , 1997 , 175-176, 720-724	1.6	23
5	Large blueshift in the photoluminescence of pseudomorphic InGaAs/GaAs quantum wells grown in patterned (100) GaAs grooves and ridges with vertical sidewalls. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996 , 14, 2312		4
4	Room-temperature operation of In _{0.4} Ga _{0.6} As/GaAs self-organised quantum dot lasers. <i>Electronics Letters</i> , 1996 , 32, 1374	1.1	182
3	Conduction band offsets in CdZnSSe/ZnSSe single quantum wells measured by deep level transient spectroscopy. <i>Applied Physics Letters</i> , 1996 , 68, 3591-3593	3.4	3
2	Adatom migration effects during molecular beam epitaxial growth of InGaAs/GaAs quantum wells on patterned substrates with vertical sidewalls: Blue shift in luminescence spectra. <i>Applied Physics Letters</i> , 1996 , 68, 1120-1122	3.4	4
1	Room temperature self-organized quantum dot transistors		1